

FEATURES

Fast Switching Speed
 For General Purpose Switching Applications
 High Conductance

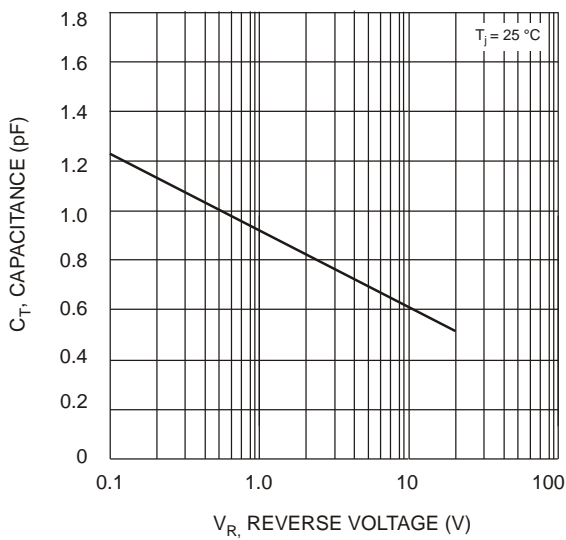
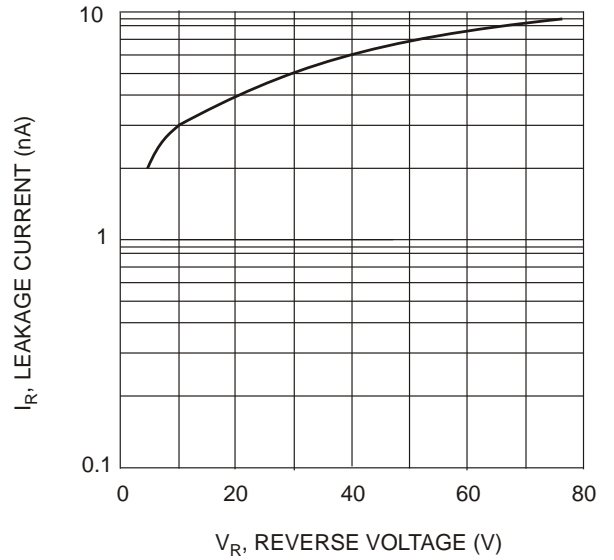
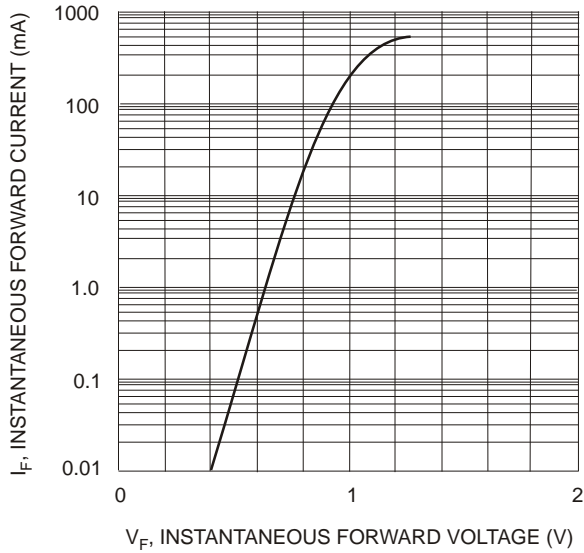
Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Continuous Reverse Voltage	V_R	75	V
Continuous Forward Current (Double Diode Loaded)	I_F	125	mA
Continuous Forward Current (Single Diode Loaded)	I_F	215	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	at $t = 1\text{ s}$ 0.5	A
		at $t = 1\text{ ms}$ 1	
		at $t = 1\text{ }\mu\text{s}$ 4.5	
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit		
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 50\text{ mA}$ at $I_F = 150\text{ mA}$	V_F	0.715 0.855 1 1.25	V		
Reverse Current at $V_R = 25\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 25\text{ V}, T_j = 150\text{ }^\circ\text{C}$ at $V_R = 75\text{ V}, T_j = 150\text{ }^\circ\text{C}$		30 1 30 50		nA μA μA μA	
Diode Capacitance at $V_R = 0, f = 1\text{ MHz}$		C_d		1.5	pF
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}, I_R = 1\text{ mA}, R_L = 100\text{ }\Omega$		t_{rr}		4	ns

Typical Characteristics





BAV99

Si ching Diode

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23

